EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3568	etch$3 with pillar	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L2	254	L1 and etch$3 with strip	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L3	27	L2 and second adj etch$3 with pillar	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L4	2	("20020028541").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L5	21	L3 and antifuse	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L6	271595	((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L7	43895	((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L8	0	((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different same (back adj to adj back))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03

L9	1731	((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different same (sequential$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L10	685	((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different same (sequential$3)) and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L11	102	(((first adj (mask or photoresist or resist or pattern)) same (second adj (mask or resist or photoresist or pattern)) same different same (sequential$3)) and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L12	0	L11 and antifuse	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L13	6	L11 and pillar	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L14	1563	pillar with memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L15	6	L13 and semiconductor and etch$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L16	1000	L14 and semiconductor and etch$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03

L17	52	pillar with memory and etch$4 with second adj direction	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L18	3568	etch$3 with pillar	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L19	254	L18 and etch$3 with strip	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L20	27	L19 and second adj etch $3 with pillar	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L21	2	("20020028541").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L22	21	L20 and antifuse	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L23	271595	(((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L24	43895	(((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L25	0	(((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different same (back adj to adj back))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03

L26	1731	((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different same (sequential$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L27	685	((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different same (sequential$3)) and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L28	102	((first adj (mask or photoresist or resist or pattern)) same (second adj (mask or resist or photoresist or pattern)) same different same (sequential$3)) and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L29	0	L28 and antifuse	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L30	6	L28 and pillar	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L31	1563	pillar with memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L32	6	L30 and semiconductor and etch$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L33	1000	L31 and semiconductor and etch$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03

L34	52	pillar with memory and etch$4 with second adj direction	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L35	275069	L18 L19 L20 L21 L22 L23 L24 L25 L26 L27 L28 L29 L30 L31 L32 L33 L34	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L36	16	"6952043"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L37	967	438/200.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L38	2291	438/197.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L39	286	438/237.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L40	8	L37 and etch$3 with pillar	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L41	24	L38 and etch$3 with pillar	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L42	6	L39 and etch$3 with pillar	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03

L43	277494	L1 L2 L3 L4 L5 L6 L7 L8 L9 L10 L11 L12 L13 L14 L15 L16 L17 L18 L19 L20 L21 L22 L23 L24 L25 L26 L27 L28 L29 L30 L31 L32 L33 L34 L35 L36 L37 L38 L39 L40 L41 L42	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:03
L44	4	"7157314"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:06
L45	102	"6514805"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:11
L46	70	pillar with ((in adj situ) or sequential$2 or (back adj to adj back)) with etch$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:42
L47	1	pillar with back adj to adj back	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:56
L48	0	etch$3 with back adj to adj back	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:56
L49	2	pattern$3 with back adj to adj back	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/13 21:57
S1	2942	etch$3 with pillar	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/23 19:10
S2	206	S1 and etch$3 with strip	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/23 19:11

S3	25	S2 and second adj etch$3 with pillar	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/23 19:38
S4	2	("20020028541").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/23 19:33
S5	20	S3 and antifuse	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/23 19:39
S6	250810	(((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/16 18:28
S7	39871	(((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/16 18:28
S8	0	(((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different same (back adj to adj back))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/16 18:28
S9	1611	(((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different same (sequential$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/16 18:29
S10	604	(((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different same (sequential$3)) and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/16 18:30

S11	88	((first adj (mask or photoresist or resist or pattern)) same (second adj (mask or resist or photoresist or pattern)) same different same (sequential$3)) and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/16 18:45
S12	0	S11 and antifuse	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/16 18:46
S13	5	S11 and pillar	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/16 18:49
S14	1365	pillar with memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/16 18:59
S15	5	S13 and semiconductor and etch$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/16 18:50
S16	862	S14 and semiconductor and etch$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/16 18:50
S17	41	pillar with memory and etch$4 with second adj direction	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/16 19:00
S18	3395	etch$3 with pillar	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:17
S19	246	S18 and etch$3 with strip	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:05

S20	26	S19 and second adj etch $3 with pillar	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:17
S21	2	("20020028541").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:05
S22	21	S20 and antifuse	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:05
S23	263959	(((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:05
S24	42311	(((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:05
S25	0	(((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different same (back adj to adj back))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:05
S26	1693	(((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different same (sequential$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:05
S27	649	(((first with (mask or photoresist or resist or pattern)) same (second with (mask or resist or photoresist or pattern)) same different same (sequential$3)) and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:05

S28	95	((first adj (mask or photoresist or resist or pattern)) same (second adj (mask or resist or photoresist or pattern)) same different same (sequential$3)) and semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:05
S29	0	S28 and antifuse	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:05
S30	6	S28 and pillar	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:08
S31	1483	pillar with memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:05
S32	6	S30 and semiconductor and etch$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:05
S33	939	S31 and semiconductor and etch$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:05
S34	48	pillar with memory and etch$4 with second adj direction	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:05
S35	267276	S18 S19 S20 S21 S22 S23 S24 S25 S26 S27 S28 S29 S30 S31 S32 S33 S34	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:05
S36	6	"6952043"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:11

S37	952	438/200.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:17
S38	2174	438/197.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:17
S39	274	438/237.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:17
S40	8	S37 and etch$3 with pillar	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:17
S41	23	S38 and etch$3 with pillar	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:17
S42	5	S39 and etch$3 with pillar	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/09 17:17

4/13/08 9:57:57 PM
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